## Surface Mount General Purpose Silicon Rectifiers Reverse Voltage - 1600 & 2000 V Forward Current - 1.0 A

#### **FEATURES**

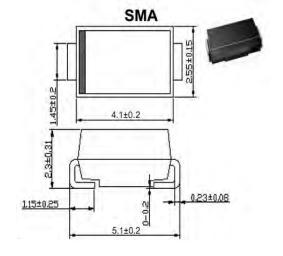
- · For surface mounted applications
- · Low profile package
- Glass Passivated Chip Juntion
- · Easy to pick and place
- Lead free in comply with EU RoHS 2011/65/EU directives

#### **MECHANICAL DATA**

· Case: SMA

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.055g / 0.002oz



### **Maximum Ratings and Electrical characteristics**

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	SM516	SM520	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	1600	2000	V
Maximum RMS voltage	$V_{RMS}$	1120	1400	V
Maximum DC blocking voltage	V <sub>DC</sub>	1600	2000	V
Maximum Average Forward Rectified Current at $T_c$ = 100 °C	I <sub>F(AV)</sub>	1.0		А
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	30		А
Maximum Instantaneous Forward Voltage at 1.5 A	V <sub>F</sub>	1.15		V
Maximum Reverse Current $T_J = 25  ^{\circ}\text{C}$ $T_J = 125  ^{\circ}\text{C}$	I <sub>R</sub>	5 50		μΑ
Typical Junction Capacitance 1)	C <sub>j</sub>	20		pF
Typical Thermal Resistance <sup>2)</sup>	$R_{\theta JA}$	95		°C/W
Operating and Storage Temperature Range	$T_{j}, T_{stg}$	-55 ~ +150		°C

<sup>1)</sup> Measured at 1 MHz and applied reverse voltage of 4 V D.C

<sup>2 )</sup> P.C.B. mounted with 0.2 X 0.2" (5 X 5 mm) copper pad areas.



# **SEMICONDUCTOR** TECHNICAL DATA

Fig.1 Forward Current Derating Curve

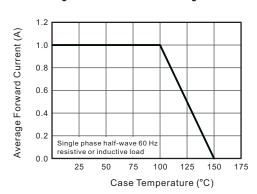


Fig.3 Typical Instaneous Forward

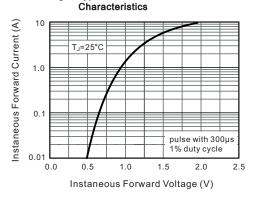


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

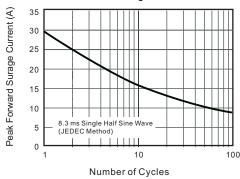


Fig.2 Typical Reverse Characteristics

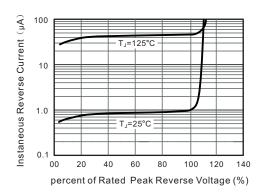


Fig.4 Typical Junction Capacitance

